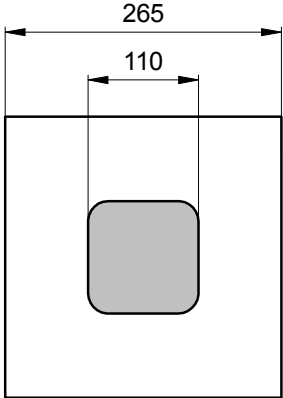


Radiation	Type	Technology	Electrodes
Yellow	Standard	AlInGaP/GaAs	P (anode) up

	typ. dimensions ( $\mu\text{m}$ )	
	<u>typ. thickness</u> 260 ( $\pm 20$ ) $\mu\text{m}$  <u>cathode</u> gold alloy, 0.5 $\mu\text{m}$  <u>anode</u> gold alloy, 1.5 $\mu\text{m}$	

### Optical and Electrical Characteristics

$T_{\text{amb}} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	$V_F$		2.0	2.3	V
Reverse voltage	$I_R = 10 \mu\text{A}$	$V_R$	5			V
Radiant power <sup>1</sup>	$I_F = 20 \text{ mA}$	$\Phi_e$	0.5	0.7		mW
Radiant power <sup>2</sup>	$I_F = 20 \text{ mA}$	$\Phi_e$		1.4		mW
Luminous intensity <sup>1</sup>	$I_F = 20 \text{ mA}$	$I_V$	75	110		mcd
Luminous intensity <sup>2</sup>	$I_F = 20 \text{ mA}$	$I_V$		200		mcd
Peak wavelength	$I_F = 20 \text{ mA}$	$\lambda_P$	592	595	598	nm
Dominant wavelength	$I_F = 20 \text{ mA}$	$\lambda_D$		592		nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		17		nm
Switching time	$I_F = 20 \text{ mA}$	$t_r, t_f$		30		ns

<sup>1</sup>Measured on bare chip on TO-18 header with *EPIGAP* equipment

<sup>2</sup>Measured on epoxy covered chip on TO-18 header with *EPIGAP* equipment

### Labeling

Type	Lot N°	$I_V(\text{typ})$ [mcd]	$V_F(\text{typ})$ [V]	Quantity
ELC-590-13				

**Packing:** Chips on adhesive film with wire-bond side on top